



#### **N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	RDS(ON) Max	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	$24m\Omega$ @ $V_{GS} = 4.5V$	6.2A
200	$32m\Omega$ @ $V_{GS} = 2.5V$	0.2A

### **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Backlighting

## **Features and Benefits**

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

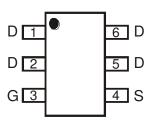
#### **Mechanical Data**

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.013 grams (Approximate)

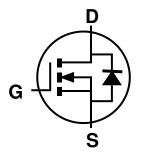
#### TSOT26



Top View



Top View Pin Configuration



**Equivalent Circuit** 

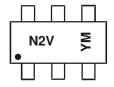
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2028UVT-7	TSOT26	3,000/Tape & Reel
DMN2028UVT-13	TSOT26	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



N2V = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	201	4	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D		Ē	F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GSS}$	±8	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	ΙD	6.2	Α
Maximum Body Diode Forward Current (Note 6)	I <sub>S</sub>	1.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	40	Α

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.2	W	
Thermal Desistance Junction to Ambient (Note E)	Steady state	Б	105	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	76	-C/VV	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.6	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	П	76		
Thermal Resistance, Junction to Ambient (Note o)	t<10s	$R_{\theta JA}$	50	°C/W	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	15		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

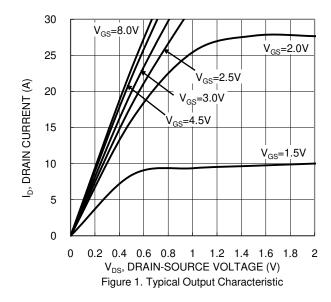
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

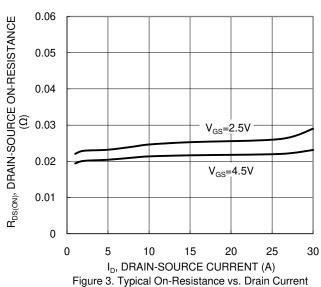
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				l .			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS} = 16V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	0.4	_	1.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			20	24	mΩ	$V_{GS} = 4.5V, I_D = 6.2A$	
Static Diani-Source On-Nesistance	R <sub>DS(ON)</sub>		24	32	11122	$V_{GS} = 2.5V, I_D = 5.2A$	
Diode Forward Voltage	$V_{SD}$		_	1.2	V	$V_{GS} = 0V, I_{S} = 1.3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		856	_		10111	
Output Capacitance	Coss		83		pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz	
Reverse Transfer Capacitance	$C_{rss}$		78	_		1 = 1.0WH12	
Total Gate Charge	$Q_g$		8.3	_			
Gate-Source Charge	$Q_{gs}$		1.3	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.2A$	
Gate-Drain Charge	$Q_{gd}$		3.1	_			
Turn-On Delay Time	t <sub>D(ON)</sub>		13.2	_			
Turn-On Rise Time	t <sub>R</sub>	_	12.6	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		65		115	$I_D = 1A$ , $R_G = 6\Omega$	
Turn-Off Fall Time	t <sub>F</sub>		22	_			

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







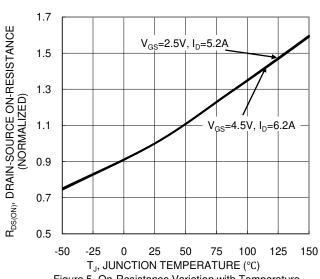
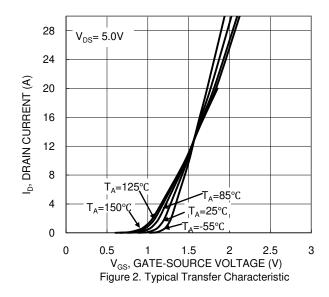
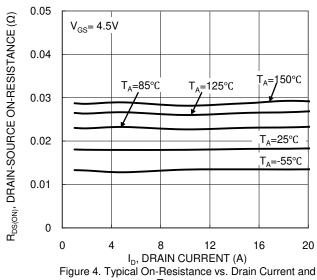


Figure 5. On-Resistance Variation with Temperature





Temperature

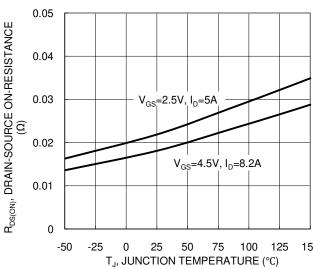
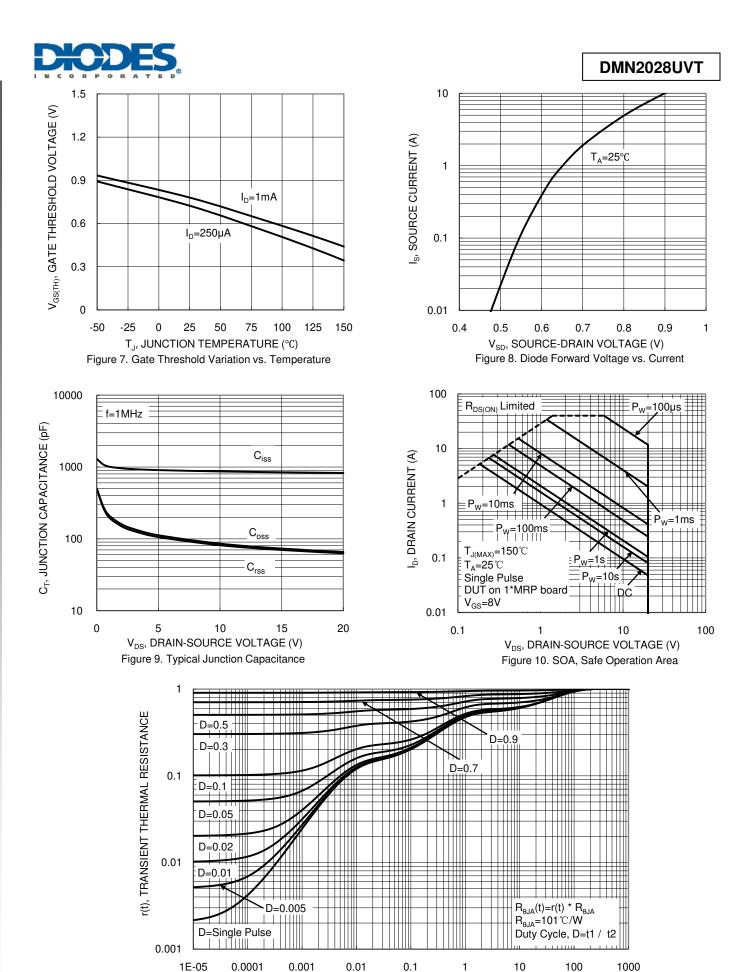


Figure 6. On-Resistance Variation with Temperature

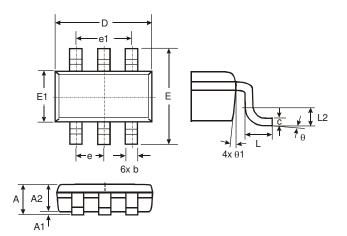


t1, PULSE DURATION TIME (sec) Figure 11. Transient Thermal Resistance



## **Package Outline Dimensions**

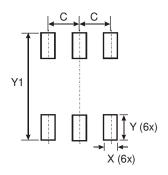
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TSOT26								
Dim	Min	Max	Тур					
Α	_	1.00	_					
A1	0.01	0.10						
A2	0.84	0.90	_					
D	_	_	2.90					
Е	_	_	2.80					
E1			1.60					
b	0.30	0.45						
С	0.12	0.20						
е			0.95					
e1			1.90					
L	0.30	0.50	_					
L2			0.25					
θ	0°	8°	4°					
θ1	4°	12°						
All Dimensions in mm								

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.950
Х	0.700
Υ	1.000
Y1	3.199



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